

AND, AT THE WAFER LEVEL

For many in the industry, performing final test at the wafer level is still a novel idea. While providing some much needed solutions, it also comes with its own set of challenges. The four papers in this session look at wafer-level test from a number of different perspectives. The first one discusses the mechanical and electrical differences between wafer-level probe and wafer-level test using spring pins, focusing on requirements for performing final test at the wafer-level. The second presentation provides a comparison between traditional probe test for an RF wafer level chip scale package (WLCSP) and a final test socket solution. TSV issues lead our third author to share technologies that can bridge between 3D stacking and the 3D IC without TSVs. Finally, we'll gain insight into what some consider the holy grail of burn-in and test – wafer-level burn-in (WLBI). Now that WLBI is possible, it's important to understand when it's appropriate to consider WLBI versus other burn-in alternatives.

Spring Probes and Probe Cards for Wafer-Level Test

Jim Brandes—Multitest

A Comparison of Probe Solutions for an RF WLCSP Product

James Migliaccio—RF Micro Devices

Bridging Between 3D and 3D TSV Stacking Technologies

Belgacem Haba, Ph.D.—Invensas



Wafer-Level Burn-in Decision Factors

Steve Steps—Aehr Test Systems

COPYRIGHT NOTICE

The paper(s) in this publication comprise the Proceedings of the 2013 BiTS Workshop. The content reflects the opinion of the authors and their respective companies. They are reproduced here as they were presented at the 2013 BiTS Workshop. This version of the papers may differ from the version that was distributed in hardcopy & softcopy form at the 2013 BiTS Workshop. The inclusion of the papers in this publication does not constitute an endorsement by BiTS Workshop, LLC or the workshop's sponsors.

There is NO copyright protection claimed on the presentation content by BiTS Workshop, LLC. (Occasionally a Tutorial and/or TechTalk may be copyrighted by the author). However, each presentation is the work of the authors and their respective companies: as such, it is strongly encouraged that any use reflect proper acknowledgement to the appropriate source. Any questions regarding the use of any materials presented should be directed to the author(s) or their companies.

The BiTS logo and 'Burn-in & Test Strategies Workshop' are trademarks of BiTS Workshop, LLC. All rights reserved.



Wafer-Level Burn-in Decision Factors

Steve Steps Aehr Test Systems



2013 BiTS Workshop March 3 - 6, 2013



Content

- Options for Burn-in
- Objective of analysis
- Scenario 1: Simple DRAM
- Scenario 2: Memory module
- Scenario 3: 3D stacked package
- Conclusions

3/2013

Wafer-Level Burn-in Decision Factors

Paper #4



And, at the Wafer Level

3

Options for Burn-In

- No burn-in
- Wafer-Level burn-in (WLBI)
- Packaged part burn-in
- Module burn-in



3/2013

Burn-in Tradeoff Summary

- No burn-in
 - If die is more reliable than needed
- WLBI
 - High die count per wafer
 - Expensive packaging (burn-in before packaging)
 - Non-repairable module
- Packaged part burn-in
 - Large die with cheap, small package
- Module burn-in
 - High die count in repairable module
 - Relatively high module-level failures

3/2013

Wafer-Level Burn-in Decision Factors



And, at the Wafer Level



Objective of Analysis

What factors determine which method of burn-in (if any) is most cost effective?

Note:

•Analysis only focuses on simple economic cost trade-offs and ignores the secondary effects of failures – which are typically significant

•All values (such as cost per die) should be used as relative measures, not absolute values

•"Your mileage may vary"

3/2013

Wafer-Level Burn-in Decision Factors



Micron

Source: Diaikey

Scenario 1: Simple DRAM

- Single, leading edge DRAM die

 About \$2 per die
 - About 750 die per wafer
- Single die per FBGA package
- Model cost versus benefit
 - Burn-in costs
 - Packaging cost savings
- Analysis ignores implications of failure; it only considers cost of replacing the failed die

3	20	13	
3/	20	10	

Wafer-Level Burn-in Decision Factors





And, at the Wafer Level

Simple DRAM Conclusions

- Burn-in savings are quite small
 - Infant mortality die are thrown away anyway
 - Savings is only packaging costs
 - Burn-in costs are much higher than savings
- Burn-in not economically justified
 - but only if the effects of failures are ignored
 - Only considered replacement of device



3/2013

3/2013

Wafer-Level Burn-in Decision Factors

Scenario 2: Memory Module

- Assumptions:
 - \$2 per memory die
 - Up to 18 die per package
- Model cost versus benefit of
 - Wafer-Level burn-in
 - Packaged Part burn-in
 - Module burn-in

Note: failure cost limited to replacement of module





Wafer-Level Burn-in Decision Factors







Paper #4 6

2013 BiTS Workshop ~ March 3 - 6, 2013





















19

Scenario 3: 3D Stacked Package

- Stacked package with:
 - \$20 microcontroller chip
 - 1 to 12 memory die @ \$2 each
 - \$5 packing cost
- Model cost per benefit varying:
 - Memory die count
 - Memory die failure rate

Note: only memory failures considered and cost of failure limited to replacement of package only

3/2013

Wafer-Level Burn-in Decision Factors

Total Burn-in Cost per Die 14.00 Assumes 1 memory die per module 12.00
 Total BI Cost per Die (cents)

 00°9
 0°0°

 0°0°
 0°0°
 -WLBI PP BI Module 2.00 0.00 9 10 4 5 6 7 8 11 12 Test and Burn-in Time (hr) 3/2013 Wafer-Level Burn-in Decision Factors 20



Paper #4 10















And, at the Wafer Level

25

3D Stack Observations

- If failure rate improvement is low enough (<0.1%) then burn-in is not justified by package replacement cost
- Burn-in decision is relatively independent of the number of memory die in the stack
 - Note this is very different from the memory module case
- Since the 3D stack is probably not repairable, wafer-level burn-in may be the only choice and is very cost effective

3/2013

Wafer-Level Burn-in Decision Factors

> Paper #4 13



And, at the Wafer Level

Overall Conclusions (2)

- Wafer-Level burn-in is likely the best choice if:
 - Die failure rate is not very low
 - High die count per wafer
 - Expensive packaging (burn-in before packaging)
 - Multiple die in a non-repairable end device
- All forms of burn-in are more justified if:
 - end application is sensitive to failures (such as automotive, medical, military, aerospace)
- WLBI can also be justified by:
 - Wafer information valuable (failure location on wafer, fab process monitoring, etc.)

3/2013

Wafer-Level Burn-in Decision Factors